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Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-3EJH01HM3/6B</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-3EJH01HM3/6B - DIODE GEN PURP 100V 3A DO221AC

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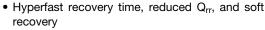
VS-3EJH01HM3

Vishay Semiconductors

Hyperfast Rectifier, 3 A FRED Pt®



FEATURE	S
 Hyperfast 	re





• 175 °C maximum operating junction temperature

• Specific for output and snubber operation

RoHS COMPLIANT HALOGEN

· Low forward voltage drop

Low leakage current

FREE · Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

PRODUCT SUMMARY				
Package	DO-221AC (SlimSMA)			
I _{F(AV)}	3 A			
V_{R}	100 V			
V _F at I _F	0.74 V			
t _{rr}	30 ns			
T _J max.	175 °C			
Diode variation	Single die			

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		100	V	
Average rectified forward current	I _{F(AV)}	T _C = 145 °C ⁽¹⁾	3	V	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	85	Α	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	100	-	-	.,
Forward voltage	V _F	I _F = 3 A	-	0.86	0.93	V
Forward voltage		I _F = 3 A, T _J = 125 °C	-	0.74	0.78	
Reverse leakage current	I _R	$V_R = V_R$ rated	-	-	2	μA
		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	0.5	8	μΑ
Junction capacitance	C _T	V _R = 100 V	-	13	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 50$	0 A/μs, V _R = 30 V	-	26	-	
Davaraa raaayany tima		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	30	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	18	-	ns
		T _J = 125 °C		-	26	-	
Dook room ourrent		T _J = 25 °C	$I_F = 3 A$	-	2.5	-	Α
Peak recovery current I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/μs V _B = 160 V	-	4	-	A	
Barrara marana da mara	T _J = 25 °C		-	23	-	nC	
Reverse recovery charge	harge Q _{rr}	T _J = 125 °C		-	50	-	nc nc

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	10	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	110	C/VV
Approximate Weight				0.032		g
Approximate Weight				0.0011		OZ.
Marking device		Case style DO-221AC (SlimSMA)		31	- 11	

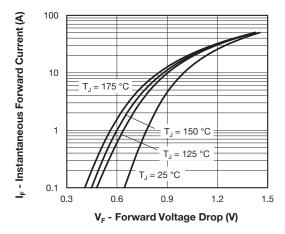


Fig. 1 - Typical Forward Voltage Drop Characteristics

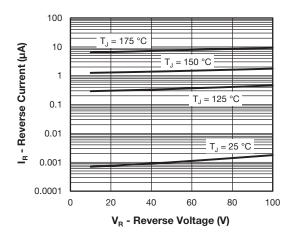


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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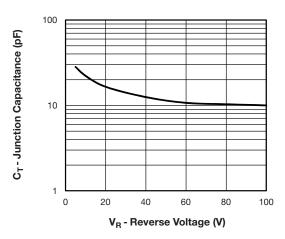


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

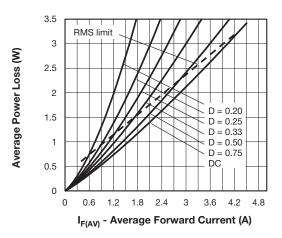


Fig. 5 - Forward Power Loss Characteristics

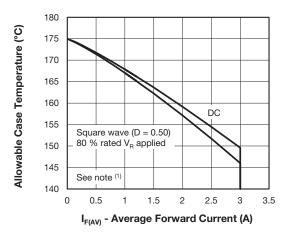


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

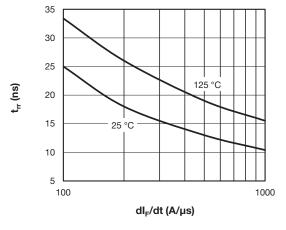


Fig. 6 - Typical Reverse Recovery vs. dl_F/dt

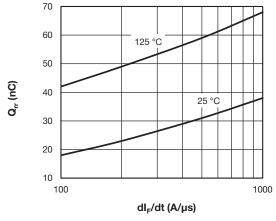


Fig. 7 - Typical Stored Charge vs. dI_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)}$ x V_{FM} at ($I_{F(AV)}$ /D) (see Fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_{R} (1 - D); I_{R} at V_{R1} = rated V_{R}

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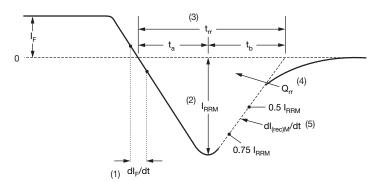
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- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

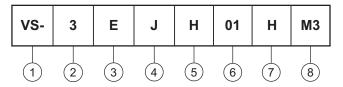
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (3 = 3 A)
- Circuit configuration:

E = single diode

- J = SlimSMA package
- Process type,

H = hyperfast recovery

- Voltage code (01 = 100 V)
- H = AEC-Q101 qualified
- M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-3EJH01HM3/6A	3500	3500	7"diameter plastic tape and reel		
VS-3EJH01HM3/6B	14 000	14 000	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95571			
Part marking information	www.vishay.com/doc?95562			
Packaging information	www.vishay.com/doc?88869			

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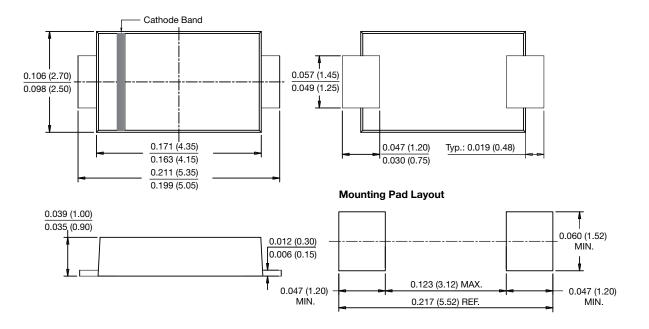


Outline Dimensions

Vishay Semiconductors

DO-221AC (SlimSMA)

DIMENSIONS in inches (millimeters)





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